DIODES INCORPORATED

BAS70TW /DW-04 / DW-05 /DW-06 /BRW

SURFACE MOUNT SCHOTTKY BARRIER DIODE ARRAYS

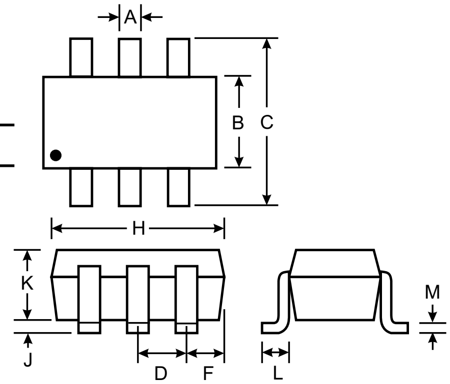
NEW PRODUCT

Features

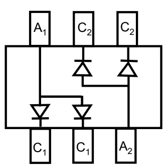
- Low Forward Voltage Drop
- Fast Switching
- Ultra-Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection

Mechanical Data

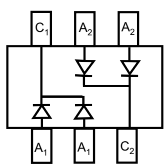
- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Orientation: See Diagrams Below
- Weight: 0.006 grams (approx.)



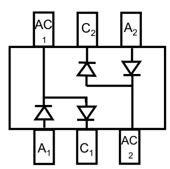
SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.80	2.20
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		



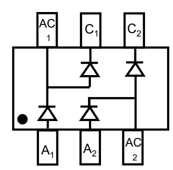
BAS70DW-06*
Marking: K76



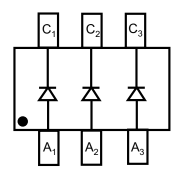
BAS70DW-05*
Marking: K71



BAS70DW-04*
Marking: K74



BAS70BRW
Marking: K75



BAS70TW
Marking: K73

*Symmetrical configuration, no orientation indicator.

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	70	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	V
Forward Continuous Current (Note 1)	I_{FM}	70	mA
Non-Repetitive Peak Forward Surge Current @ t < 1.0s	I_{FSM}	100	mA
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance Junction to Ambient Air (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage Temperature Range	T_j T_{STG}	-55 to +125 -65 to +125	°C

Electrical Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Maximum Forward Voltage	V_{FM}	—	410 1000	mV mV	t_p <300µs, I_F = 1.0mA t_p <300µs, I_F = 15mA
Maximum Peak Reverse Current	I_{RM}	—	100	nA	t_p < 300µs, V_R = 50V
Junction Capacitance	C_j	—	2.0	pF	V_R = 0V, f = 1.0MHz
Reverse Recovery Time	t_{rr}	—	5.0	ns	$I_F = I_R$ = 10mA to I_R = 1.0mA, Irr = 0.1 x I_R, R_L = 100Ω

Notes: 1. Valid Provided that terminals are kept at ambient temperature.